



SOT-23 Plastic-Encapsulate Transistors

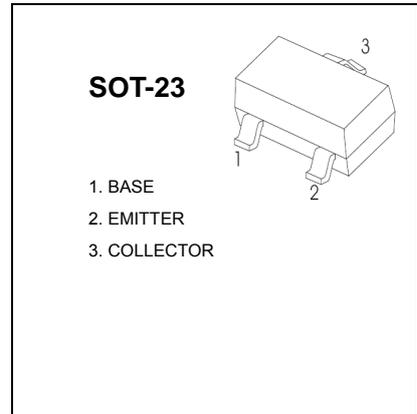
BF821/BF823 TRANSISTOR (PNP)

FEATURES

- Low current (max.-50 mA)
- High voltage (max.-300V)
- Telephony and professional communication equipment.

MARKING: BF821:1W, BF823: 1Y

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)



Symbol	Parameter	Value	Unit	
V _{CB0}	Collector-Base Voltage	BF821 BF823	-300 -250	V
V _{CEO}	Collector-Emitter Voltage	BF821 BF823	-300 -250	V
V _{EBO}	Emitter-Base Voltage		-5	V
I _C	Collector Current -Continuous		-50	mA
P _C	Collector Power Dissipation		0.25	W
T _j	Junction Temperature		150	°C
T _{stg}	Storage Temperature		-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	BF821 BF823	-300 -250	V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	BF821 BF823	-300 -250	V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0		-5	V
Collector cut-off current	I _{CBO}	V _{CB} =-200V, I _E =0		-0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-0.05	μA
DC current gain	h _{FE}	V _{CE} = -20V, I _C =-25mA	50		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-30mA, I _B = -5mA		-0.8	V
Transition frequency	f _T	V _{CE} =-10V, I _C = -10mA, f=100MHz	60		MHz
Collector output capacitance	C _{ob}	V _{CB} =-30V, I _E =0, f=1MHz		1.6	pF